Compact Hierarchical Bipolar Transistor Modeling with HICUM will be of great practical benefit to professionals from the modeling, circuit design, and process development community who are interested in the application of bipolar transistors, which include SiGe:C HBTs fabricated with existing cutting-edge process technology. The book begins with an overview on the different device designs of modern bipolar transistors, along with their relevant operating conditions, and a review of mostly classical theories that are brought into context with modern technology. The subsequent chapters cover advanced theory that is required for understanding modern device designs which include such aspects as temperature dependence, geometry scaling, and noise. This book aims to provide a solid basis for the understanding of modern bipolar transistors and uses HICUM as a vehicle for model building.

Readership: R&D professionals and modeling/SPICE engineers in the semiconductor industry; graduate, research students, and faculties at universities.

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